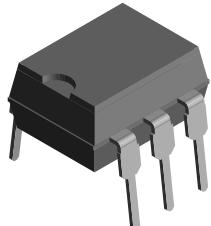
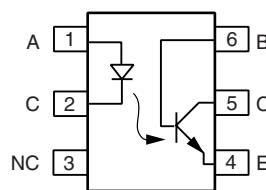


## Optocoupler, Phototransistor Output, with Base Connection, 300 V BV<sub>CCEO</sub>



i179004



### FEATURES

- Good CTR linearity with forward current
- Low CTR degradation
- Very high collector emitter breakdown voltage,  $BV_{CER} = 300$  V
- Isolation test voltage: 5300 V<sub>RMS</sub>
- Low coupling capacitance
- High common mode transient immunity
- Phototransistor optocoupler 6 pin DIP package with base connection
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


**RoHS**  
COMPLIANT

### DESCRIPTION

The SFH 640 is an optocoupler with very high  $BV_{CER}$ , a minimum of 300 V. It is intended for telecommunications applications or any DC application requiring a high blocking voltage.

### AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

### ORDER INFORMATION

PART	REMARKS
SFH640-1	CTR 40 to 80 %, DIP-6
SFH640-2	CTR 63 to 125 %, DIP-6
SFH640-3	CTR 100 to 200 %, DIP-6
SFH640-2X007	CTR 63 to 125 %, SMD-6 (option 7)
SFH640-3X007	CTR 100 to 200 %, SMD-6 (option 7)
SFH640-3X009	CTR 100 to 200 %, SMD-6 (option 9)

### Note

For additional information on the available options refer to option information.

### ABSOLUTE MAXIMUM RATINGS (1)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		V <sub>R</sub>	6.0	V
DC forward current		I <sub>F</sub>	60	mA
Surge forward current	t <sub>p</sub> ≤ 10 μs	I <sub>FSM</sub>	2.5	A
Total power dissipation		P <sub>diss</sub>	100	mW
<b>OUTPUT</b>				
Collector emitter voltage		V <sub>CE</sub>	300	V
Collector base voltage		V <sub>CBO</sub>	300	V
Emitter base voltage		V <sub>EBO</sub>	7.0	V
Collector current		I <sub>C</sub>	50	mA
Surge collector current	t <sub>p</sub> ≤ 10 ms	I <sub>C</sub>	100	mA
Total power dissipation		P <sub>diss</sub>	300	mW

**ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>COUPLER</b>				
Isolation test voltage between emitter and detector, refer to climate DIN 40046, part 2, Nov. 74		V <sub>ISO</sub>	5300/7500	V <sub>RMS</sub> /V <sub>PK</sub>
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω
Insulation thickness between emitter and detector			≥ 0.4	mm
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175	
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C
Operating temperature range		T <sub>amb</sub>	- 55 to + 100	°C
Soldering temperature <sup>(2)</sup>	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T <sub>sld</sub>	260	°C

**Notes**(1) T<sub>amb</sub> = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

**ELECTRICAL CHARACTERISTICS**

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	I <sub>F</sub> = 10 mA		V <sub>V</sub>		1.1	1.5	V
Reverse voltage	I <sub>R</sub> = 10 μA		V <sub>R</sub>	6.0			V
Reverse current	V <sub>R</sub> = 6.0 V		I <sub>R</sub>		0.01	10	μA
Capacitance	V <sub>F</sub> = 0 V, f = 1.0 MHz		C <sub>O</sub>		25		pF
Thermal resistance			R <sub>thja</sub>		750		K/W
<b>OUTPUT</b>							
Collector emitter breakdown voltage	I <sub>CE</sub> = 1.0 mA, R <sub>BE</sub> = 1.0 MΩ		BV <sub>CER</sub>	300			V
Voltage emitter base	I <sub>EB</sub> = 10 μA		BV <sub>BEO</sub>	7.0			V
Collector emitter capacitance	V <sub>CE</sub> = 10 V, f = 1.0 MHz		C <sub>CE</sub>		7.0		pF
Collector base capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		C <sub>CB</sub>		8.0		pF
Emitter base capacitance	V <sub>EB</sub> = 5.0 V, f = 1.0 MHz		C <sub>EB</sub>		38		pF
Thermal resistance			R <sub>thja</sub>		250		K/W
<b>COUPLER</b>							
Coupling capacitance			C <sub>c</sub>		0.6		pF
Saturation voltage collector emitter	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 2.0 mA	SFH640-1	V <sub>CEsat</sub>		0.25	0.4	V
	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 3.2 mA	SFH640-2	V <sub>CEsat</sub>		0.25	0.4	V
	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 5.0 mA	SFH640-3	V <sub>CEsat</sub>		0.25	0.4	V
Collector emitter leakage current	V <sub>CE</sub> = 200 V, R <sub>BE</sub> = 1.0 MΩ		I <sub>CER</sub>		1.0	100	nA

**Note**T<sub>amb</sub> = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

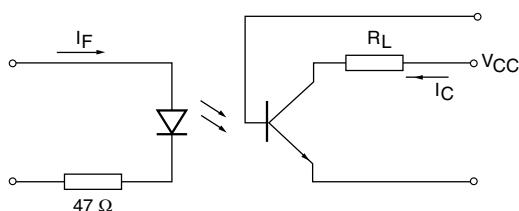
**CURRENT TRANSFER RATIO**

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	SFH640-1	I <sub>C</sub> /I <sub>F</sub>	40		80	%
	I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 10 V	SFH640-1	I <sub>C</sub> /I <sub>F</sub>	13	30		%
	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	SFH640-2	I <sub>C</sub> /I <sub>F</sub>	63		125	%
	I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 10 V	SFH640-2	I <sub>C</sub> /I <sub>F</sub>	22	45		%
	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	SFH640-3	I <sub>C</sub> /I <sub>F</sub>	100		200	%
	I <sub>F</sub> = 1.0 mA, V <sub>CE</sub> = 10 V	SFH640-3	I <sub>C</sub> /I <sub>F</sub>	34	70		%

**SWITCHING CHARACTERISTICS**

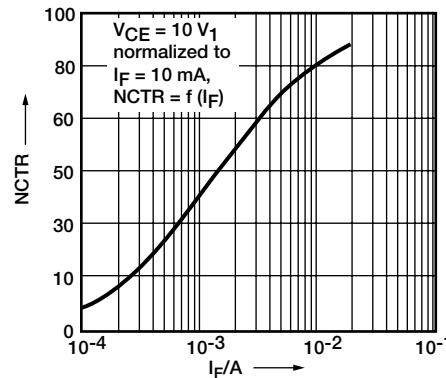
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Turn-on time	I <sub>C</sub> = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 10 V	t <sub>on</sub>		5.0		μs
Rise time	I <sub>C</sub> = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 10 V	t <sub>r</sub>		2.5		μs
Turn-off time	I <sub>C</sub> = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 10 V	t <sub>off</sub>		6.0		μs
Fall time	I <sub>C</sub> = 2.0 mA, R <sub>L</sub> = 100 Ω, V <sub>CC</sub> = 10 V	t <sub>f</sub>		5.5		μs

**TYPICAL CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified


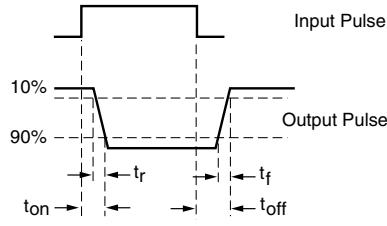
isfh640\_01a

Fig. 1 - Switching Times Measurement Test Circuit and Waveform



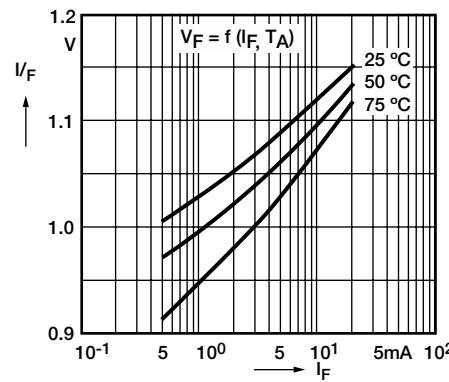
isfh640\_02

Fig. 3 - Current Transfer Ratio (Typ.)



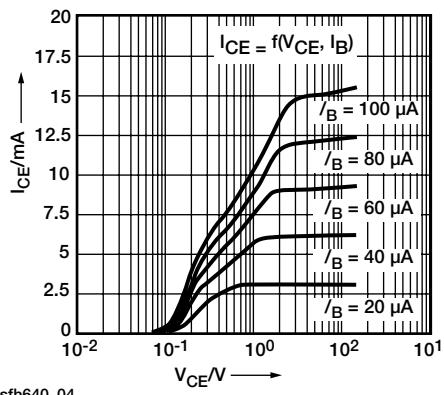
isfh640\_01b

Fig. 2 - Switching Times Measurement Test Circuit and Waveform



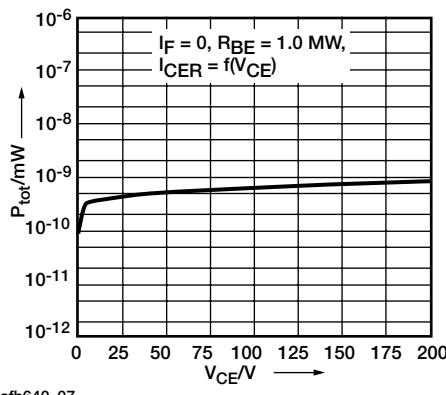
isfh640\_03

Fig. 4 - Diode Forward Voltage (Ttyp.)



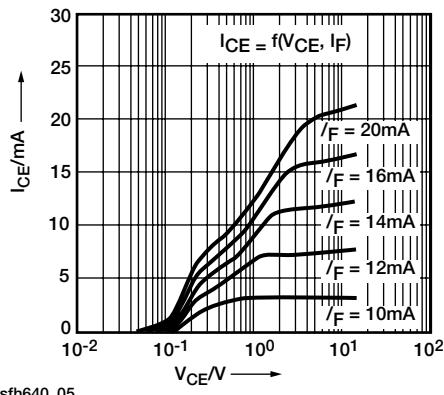
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Fig. 5 - Output Characteristics (Typ.)



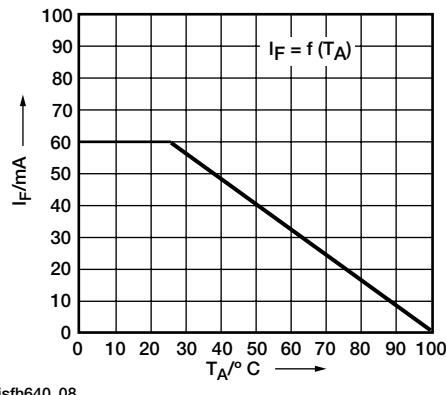
isfh640\_07

Fig. 8 - Collector-Emitter Leakage Current (Typ.)



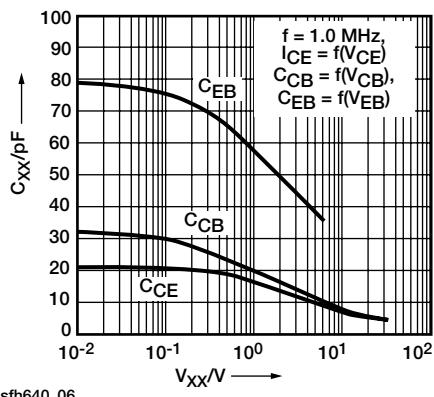
isfh640\_05

Fig. 6 - Output Characteristics (Typ.)



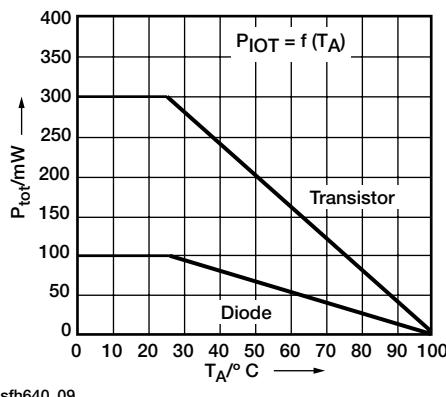
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Fig. 9 - Permissible Loss Diode



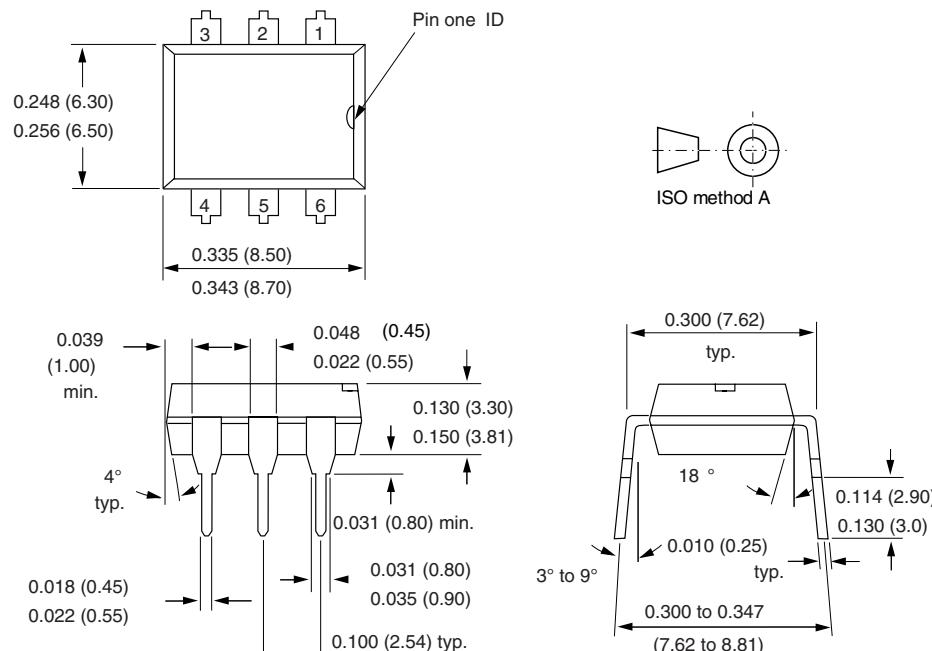
isfh640\_06

Fig. 7 - Transistor Capacitances (Typ.)

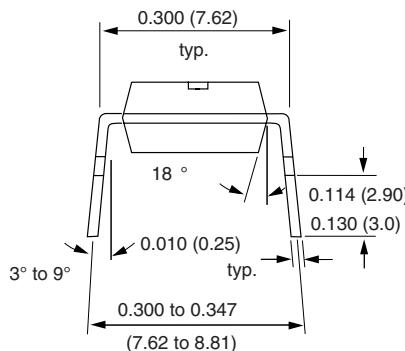
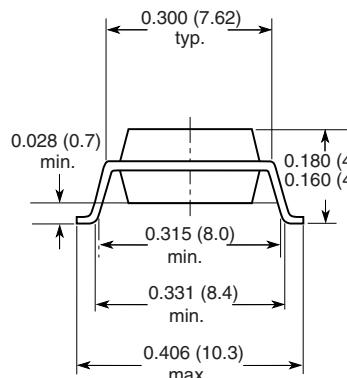
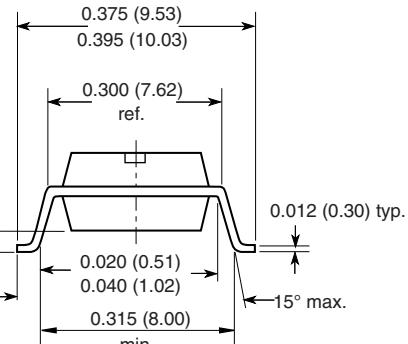


isfh640\_09

Fig. 10 - Permissible Power Dissipation

**PACKAGE DIMENSIONS** in inches (millimeters)


i178004


**Option 7**

**Option 9**


18494

**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

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1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design  
and may do so without further notice.

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"LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

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С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибуторских договоров

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- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
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- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

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- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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